

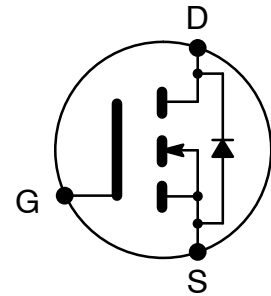


**ELECTRONICS, INC.**  
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**NTE2922  
 MOSFET  
 N-Ch, Enhancement Mode  
 High Speed Switch  
 TO3P Type Package**

**Features:**

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



**Absolute Maximum Ratings:**

Continuous Drain Current ( $V_{GS} = 10V$ ), $I_D$	
$T_C = +25^\circ C$ .....	16A
$T_C = +100^\circ C$ .....	10A
Pulsed Drain Current (Note 1), $I_{DM}$ .....	64A
Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	180W
Gate-to-Source Voltage, $V_{GS}$ .....	$\pm 20$
Single Pulse Avalanche Energy (Note 2), $E_{AS}$ .....	390mJ
Avalanche Current (Note 1), $I_{AR}$ .....	16A
Repetitive Avalanche Energy (Note 1), $E_{AR}$ .....	19mJ
Peak Diode Recovery dv/dt (Note 3), dv/dt .....	4V/ns
Operating Junction Temperature Range, $T_J$ .....	$-55^\circ$ to $+150^\circ C$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ C$
Lead Temperature (During Soldering, 1.6mm from case for 10sec), $T_L$ .....	$+300^\circ C$
Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	0.7°C/W
Thermal Resistance, Junction-to-Ambient, $R_{thJA}$ .....	30°C/W

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2.  $V_{DD} = 50V$ , starting  $T_J = +25^\circ C$ ,  $L = 2.7mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 16A$

Note 3.  $I_{SD} \leq 16A$ ,  $di/dt \leq 200A/\mu s$ ,  $V_{DD} \leq 400V$ ,  $T_J \leq +150^\circ C$

**Electrical Characteristics:** ( $T_J = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	400	-	-	V
Breakdown Voltage Temp. Coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_J}$	Reference to $+25^\circ\text{C}$ , $I_D = 1\text{mA}$	-	0.51	-	$V/^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 8.9A$	-	-	0.30	$\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
Forward Transconductance	$g_{fs}$	$V_{DS} = 40V, I_D = 8A$	8	-	-	S
Drain-to-Source Leakage Current	$I_{DSS}$	$V_{DS} = 400V, V_{GS} = 0V$	-	-	25	$\mu A$
Gate-to-Source Forward Leakage	$I_{GSS}$	$V_{GS} = 20V, V_{DS} = 0$	-	-	100	nA
Gate-to-Source Reverse Leakage	$I_{GSS}$	$V_{GS} = -20V, V_{DS} = 0$	-	-	-100	nA
Total Gate Charge	$Q_g$	$I_D = 16A, V_{DS} = 320V, V_{GS} = 10V,$ Note 4	-	-	150	nC
Gate-to-Source Charge	$Q_{gs}$		-	-	23	nC
Gate-to-Drain ("Miller") Charge	$Q_{gd}$		-	-	80	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200V, I_D = 16A, R_G = 6.2\Omega,$ $R_D = 12\Omega, \text{Note 4}$	-	16	-	ns
Rise Time	$t_r$		-	49	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	87	-	ns
Fall Time	$t_f$		-	47	-	ns
Internal Drain Inductance	$L_D$	Between lead, .250in. (6.0) mm from package and center of die contact	-	5.0	-	nH
Internal Source Inductance	$L_S$		-	13	-	nH
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	-	2600	-	pF
Output Capacitance	$C_{oss}$		-	660	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	250	-	pF

**Source-Drain Ratings and Characteristics:**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	$I_S$		-	-	16	A
Pulsed Source Current (Body Diode)	$I_{SM}$	Note 1	-	-	64	A
Diode Forward Voltage	$V_{SD}$	$T_J = +25^\circ\text{C}, I_S = 16A, V_{GS} = 0V$	-	-	1.6	V
Reverse Recovery Time	$t_{rr}$	$T_J = +25^\circ\text{C}, I_F = 16A,$ $di/dt = 100A/\mu s, \text{Note 4}$	-	380	570	ns
Reverse Recovery Charge	$Q_{rr}$		-	4.7	7.1	$\mu C$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

